

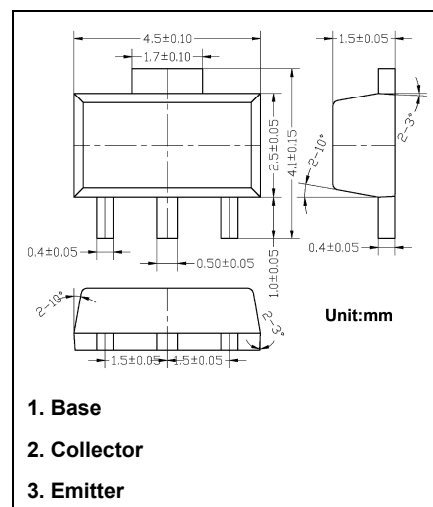
SOT-89 Plastic-Encapsulate Transistors

2SD882 NPN Transistors

Features

- Power dissipation

Marking: D882



Maximum Ratings (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector Base Voltage	40	V
V _{CEO}	Collector Emitter Voltage	30	V
V _{EBO}	Emitter Base Voltage	6	V
I _c	Collector Current - Continuous	3.0	A
P _c	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	250	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 ~ +150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _c = 100μA, I _E = 0	40			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _c = 10mA, I _B = 0	30			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E = 100μA, I _C = 0	6			V
I _{CBO}	Collector cut-off current	V _{CB} = 40V, I _E = 0			1	μA
I _{CEO}	Collector cut-off current	V _{CE} = 30V, I _B = 0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} = 6V, I _C = 0			1	μA
h _{FE(1)}	DC current gain	V _{CE} = 5V, I _c = 1mA	60			
h _{FE(2)}		V _{CE} = 5V, I _c = 10mA	50			
h _{FE(3)}		V _{CE} = 2V, I _c = 1A	60		400	
h _{FE(4)}		V _{CE} = 2V, I _c = 20mA	60			
h _{FE(5)}		V _{CE} = 2V, I _c = 100mA	32			
V _{CE(sat)}	Collector-emitter saturation voltage	I _c = 2.0A, I _B = 200mA			0.5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _c = 2.0A, I _B = 200mA			1.5	V
f _t	Transition frequency	V _{CE} = 5V, I _c = 0.1A, f = 10MHz	50			MHz

Classification OF h_{FE(1)}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Typical Characteristics

